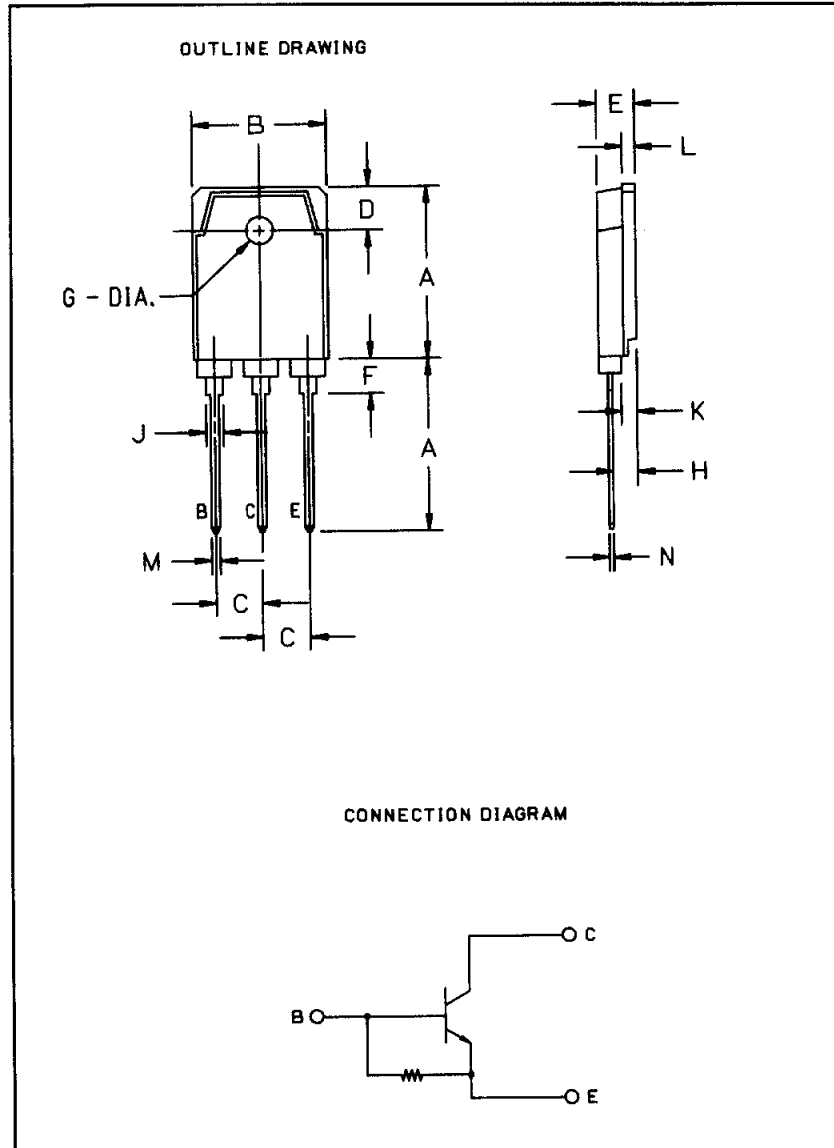


Base Drive Transistor Module 5 Amperes/1200 Volts



Outline Drawing

Dimensions	Inches	Millimeters
A	0.787	20
B	0.614	15.6
C	0.214 ± 0.008	5.45 ± 0.2
D	0.197	5
E	0.177	4.5
F	1.157	4
G	0.126 ± 0.008 Dia.	3.2 ± 0.2 Dia.

Dimensions	Inches	Millimeters
H	0.110	2.8
J	0.079	2
K	0.071	1.8
L	0.059	1.5
M	0.039	1
N	0.024	0.6

Description:

The Powerex Base Drive Transistor Modules are high power devices designed for use in switching applications or base drive amplifiers. The modules are isolated, consisting of one Bi-polar Transistor with a base-to-emitter resistor.

Features:

- ☐ Non-Isolated Mounting
- ☐ Planar Chip
- ☐ High Gain (h_{FE})
- ☐ Base-Emitter Resistor

Applications:

- ☐ Inverters
- ☐ DC Motor Control
- ☐ Switching Power Supplies
- ☐ AC Motor Control
- ☐ Base Drive

Ordering Information:

Example: Select the complete eight digit module part number you desire from the table - i.e. KS0312A01 is a 1200 Volt, 5 Ampere Base Drive Transistor Module.

Type	$V_{CE0(sus)}$ Volts (X 100)	Current Rating Amperes (0)
KS03	12	A0



Powerex, Inc., 200 Hillis Street, Youngwood, Pennsylvania 15697-1800 (412) 925-7272

KS0312A0
Base Drive Transistor Module
5 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	KS0312A0	Units
Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Sustaining Voltage, $V_{\text{BE}} = -2\text{VA}$	$V_{\text{CEV(sus)}}$	1200	Volts
Collector-Base Voltage	V_{CBO}	1200	Volts
Emitter-Base Voltage	V_{EBO}	7	Volts
Collector-Emitter Voltage	V_{CEV}	1200	Volts
Continuous Collector Current	I_{C}	5	Amperes
Continuous Base Current	I_{B}	3	Amperes
Power Dissipation	P_t	100	Watts
Max. Mounting Torque M3 Mounting Screws	—	3	in.-lb.
Modular Weight (Typical)	—	5	Grams
V Isolation	V_{RMS}	2500	Volts



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KS0312A0

Base Drive Transistor Module

5 Amperes/1200 Volts

Electrical Characteristics, $T_J = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector Cutoff Current	I_{CEV}	$V_{CE} = 1200V, V_{BE} = -2V$	—	—	1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 7V$	—	—	50	mA
DC Current Gain	h_{FE}	$I_C = 2A, V_{CE} = 5.0V$	10	—	—	—
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2A, I_B = 0.4A$	—	—	1.0	Volts
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 2A, I_B = 0.4A$	—	—	1.5	Volts
Resistive	Turn-on	t_{on}	$V_{CC} = 600V$	—	—	1.0 μs
Load	Storage Time	t_s	$I_C = 3A$	—	—	4.0 μs
Switch Times	Fall Time	t_f	$I_{B1} = 0.6, -I_{B2} = 1.2A$	—	—	0.8 μs

Thermal and Mechanical Characteristics, $T_J = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Case-to-Sink	$R_{\theta(c-s)}$	—	—	—	0.5	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta(j-c)}$	—	—	—	1.25	$^\circ\text{C/W}$

KS0312A0
Base Drive Transistor Module
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